

20V N-Channel Enhancement Mode MOSFET MAIN CHARACTERISTICS

Ι _D	6.8A		
V _{DSS}	20V		
R _{DSON} -typ(@V _{GS} =4.5V)	<31.8mΩ <mark>(Typ:18mΩ)</mark>		
R _{DSON} -typ(@V _{GS} =2.5V)	<35.6mΩ (Typ:23mΩ)		
R _{DSON} -typ(@V _{GS} =1.8V)	<41.4mΩ <mark>(Typ:30mΩ)</mark>		

Features

TrenchFET Power MOSFETLoad Switch for Portable Devices.DC/DC Converter.

Mechanical Data

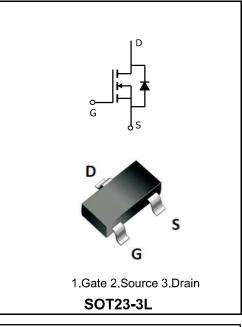
SOT23-3L Small Outline Plastic Package.Epoxy UL: 94V-0.Mounting Position: Any.

Maximum Ratings & Thermal Characteristics

Ratings at 25° C ambient temperature unless otherwise specified.

Parameters	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	20	v
Gate-Source Voltage	V _{GS}	±12	v
Continuous Drain Current t=5s	ID	6.8	
Pulsed Drain Current(note1)	І _{DM}	20	
Continuous Source-Drain Diode Current	ls	1.04	A
Power Dissipation t=5s	PD	350	mW
Junction Temperature	Tj	150	ĉ
Storage Temperature	T _{stg}	-55-+150	°C
Thermal Resistance From Junction to Ambient (note 2)	Reja	357	ଂC/ W

YFW2312MI SOT23-3L



Marking Code			
YFW2312MI	S12		



Electrical Characteristics

Ratings at 25° C ambient temperature unless otherwise specified.

Parameter	Symbols	Test Condition	Limits			Unit
	Symbols		Min	Тур	Max	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	20	-	-	v
Gate-Threshold voltage	V _{GS (th)}	$V_{DS}=V_{GS}$, $I_D=250$ uA	0.5	0.7	1.2	v
Gate-body Leakage	IGSS	V _{DS} =0V, V _{GS} =±8V	-	-	±100	nA
Zero Gate Voltage Drain current	DSS	V _{DS} =20V, V _{GS} =0V	-	-	1	uA
Drain-Source On-Resistance(note3)		Vgs=4.5V, ID=5A	-	18	31.8	mΩ
	R _{DS(ON)}	Vgs=2.5V, Ic=4.7A	-	23	35.6	mΩ
		Vgs=1.8V, Ic=4.3A	-	30	41.4	mΩ
Forward trans conductance(note3)	g fs	V _{DS} =10V, I _D =5A	-	6	-	S
Body diode voltage(note3)	V _{SD}	I _S =6.8A, V _{GS} =0V	-	0.75	1.2	v
Input capacitance	Ciss	Ciss		865	-	
Output capacitance	Coss	V _{DS} =10V, V _{GS} =0V,f=1MHz	-	105	-	pF
Reverse Transfer capacitance	C _{rss}		-	55	-	
Gate resistance	Rg	f=1MHz	0.5	-	4.8	Ω
Turn-on Time	t _{d(on)}	VDD=10V, RL=2.2Ω, VGEN=5V, ID=4A, RG=1Ω	-	-	10	
Rise time	tr		-	-	20	1
Turn-off Time	t _{d(off)}		-	-	32	– ns
Fall time	t _f	1	-	-	12	1

Notes: 1. Repetitive rating: Pulse width limited by junction temperature. 2. Surface mounted on FR4 board, t≤10s.

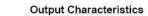
3.Pulse Test: Pulse Width ≤300us, Duty Cycle≤2%.

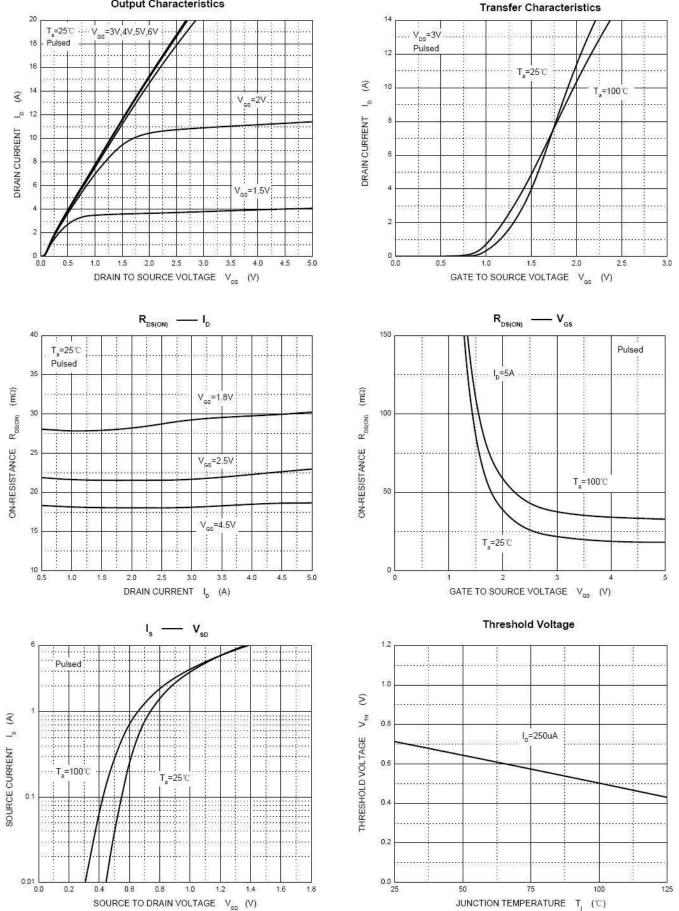
4. Guaranteed by design, not subject to producting.



Ratings and Characteristic Curves

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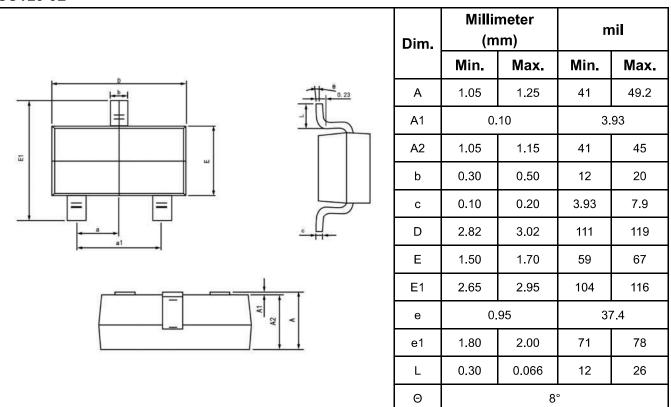


Ordering information

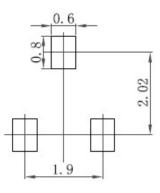
Package	Packing Description	Base Quantity	Packing Quantity
SOT23-3L	Tape/Reel,7"reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

Package Dimensions

SOT23-3L



The recommended mounting pad size





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